

1MBH20D-060

Molded IGBT

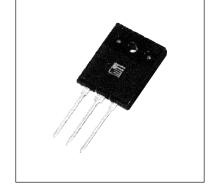
600V / 20A Molded Package

■ Features

- · Small molded package
- · Low power loss
- · Soft switching with low switching surge and noise
- High reliability, high ruggedness (RBSOA, SCSOA etc.)
- · Comprehensive line-up

■ Applications

- Inverter for Motor drive
- · AC and DC Servo drive amplifier
- Uninterruptible power supply



■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings (Tc=25°C)

Items			Symbols	Ratings	Units
Collector-Emitter Voltage			Vces	600	V
Gate-Emitter Voltage			VGES	±20	V
Collector Current	DC	TC=25°C	IC25	45	Α
		TC=110°C	IC110	20	Α
	1ms	TC=25℃	Icp	152	Α
IGBT Max. Power Dissipation			Pc	170	W
FWD Max. Power Dissipation			Pc	95	W
Operating Temperature			Tj	+150	°C
Storage Temperature			Tstg	-40 to +150	°C
Mounting Screw Torque			_	70	N⋅cm

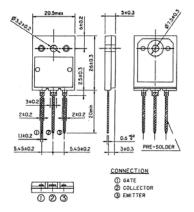
● Electrical Characteristics (at Tc=25°C unless otherwise specified)

Items		Cumbala	Characteristics			Conditions	Unita
		Symbols	min.	typ.	max.	Conditions	Units
Zero gate voltage Collector Current		Ices	ı	_	1.0	VGE = 0V, VCE = 600V	mA
Gate-Emitter leakage Current		Iges	ı	_	20	$V_{CE} = 0V$, $V_{GE} = \pm 20V$	μΑ
Gate-Emitter Threshold Voltage		V _{GE(th)}	5.5	_	8.5	VcE = 20V, Ic = 20mA	V
Collector-Emitter Saturation Voltage		V _{CE(sat)}	_	_	3.0	Vge = 15V, Ic = 20A	V
Input capacitance		Cies	_	1300	_	V _{GE} = 0V	pF
Output capacitance		Coes	_	300	_	Vce = 10V	
Reverse transfer capacitance		Cres	_	70	_	f = 1MHz	
Switching Time	Turn-on time	ton	_	_	1.2	Vcc = 300V	μs
		tr	_	_	0.6	Ic = 20A V _{GE} = ±15V	
	Turn-off time	toff	_	_	1.0	$R_G = 120\Omega$	
		tf	_	_	0.35	(Half Bridge)	
	Turn-on time	ton	_	0.16	_	Vcc = 300V	
		tr	_	0.11	_	Ic = 20A V _{GE} = +15V	
	Turn-off time	toff	_	0.30	_	$R_G = 12\Omega$	
		tf	_	_	0.35	(Half Bridge)	
FWD forward voltage drop		VF	_	_	3.0	IF = 20A	V
Reverse recovery time trr		trr	_	_	0.3	I _F = 20A, V _{GE} = -10V VR = 200V di/dt = 100A/μs	μs

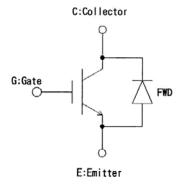
Thermal resistance Characteristics

Items	Symbols	Characteristics			Conditions	Units
items		min.	typ.	max.	Conditions	Ullits
Thermal resistance	Rth(j-c)	_	_	0.73	IGBT	°C/W
Thermal resistance	Rth(j-c)	-	_	1.31	FWD	

■ Outline drawings, mm



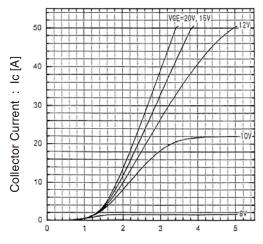
■ Equivalent circuit



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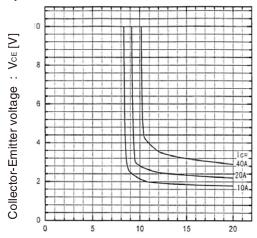
■ Characteristics

Collector current vs. Collector-Emitter voltage $Tj = 25^{\circ}C$



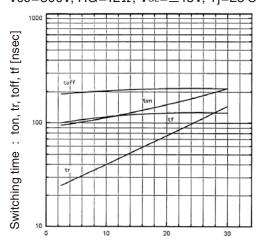
Collector-Emitter voltage : VCE [V]

Collector-Emitter voltage vs. Gate-Emitter Voltage $Tj = 25^{\circ}C$



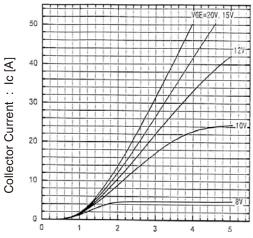
Gate-Emitter voltage: VgE [V]

Switching time vs. Collector current Vcc=300V, RG=12 Ω , VgE= \pm 15V, Tj=25 $^{\circ}$ C



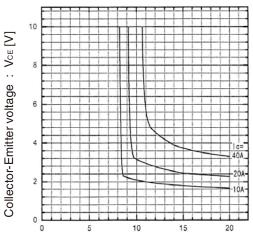
Collector current: Ic [A]

Collector current vs. Collector-Emitter voltage $Tj = 125^{\circ}C$



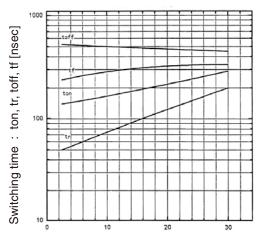
Collector-Emitter voltage: VCE [V]

Collector-Emitter voltage vs. Gate-Emitter Voltage $Tj = 125^{\circ}C$



Gate-Emitter voltage: VgE [V]

Switching time vs. Collector current Vcc=300V, $RG=12\Omega$, $V_{GE}=\pm15V$, $Tj=125^{\circ}C$

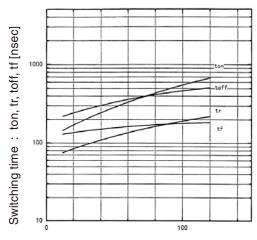


Collector current: Ic [A]

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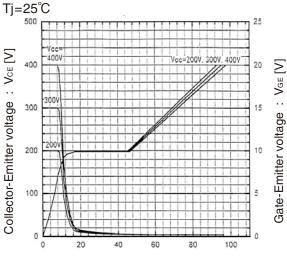
■ Characteristics

Switching time vs. RG Vcc=300V, IC=20A, VgE= \pm 15V, Tj=25°C



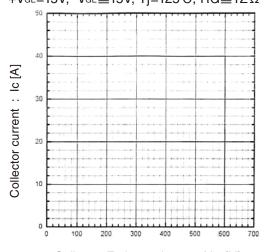
Gate resistance : $RG[\Omega]$

Dynamic input characteristics



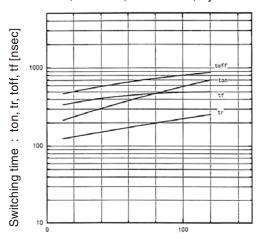
Gate charge: Qg [nQ]

Reverse Biased Safe Operating Area +V_{GE}=15V, -V_{GE}≦15V, Tj=125°C, RG≧12Ω



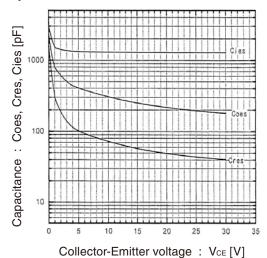
Collector-Emitter voltage : $V_{CE}[V]$

Switching time vs. RG Vcc=300V, IC=20A, VGE= \pm 15V, Tj=125°C

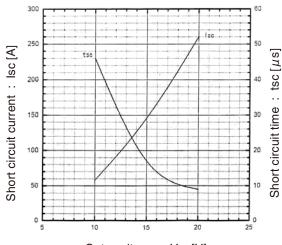


Gate resistance : RG $[\Omega]$

Capacitance vs. Collector-Emitter voltage Tj=25°C



Typical short circuit capability Vcc=400V, RG=12 Ω , Tj=125 $^{\circ}$ C

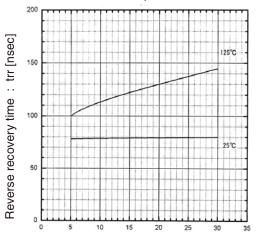


Gate voltage: VgE [V]

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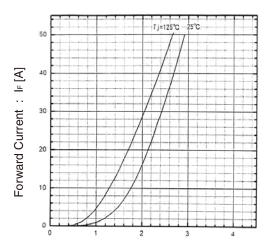
■ Characteristics

Reverse recovery time vs. Forward current VR=200V, $-di/dt=100A/\mu sec$



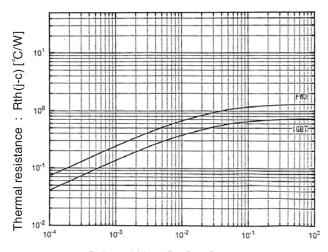
Forward current : IF [A]

Forward voltage vs. Forward current



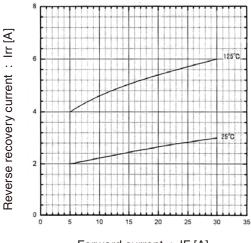
Forward Voltage: V_F[V]

Transient thermal resistance



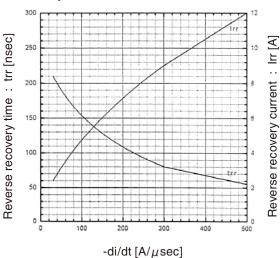
Pulse width: Pw [sec]

Reverse recovery current vs. Forward current VR=200V, $-di/dt=100A/\mu sec$



Forward current: IF [A]

Reverse recovery chracteristics vs. -di/dt I=20A, Tj=125°C



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